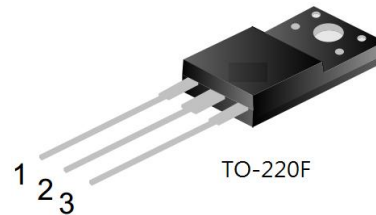
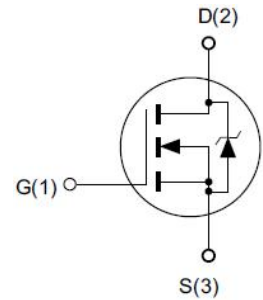


Features

- ◆ 500V, 5A, $R_{DS(ON)}(Typ.) = 1.55\Omega @ V_{GS} = 10V$.
- ◆ Low C_{rss}
- ◆ Fast Switching
- ◆ 100% Avalanche Tested

Application

- ◆ Adaptor
- ◆ Standby Power
- ◆ Switching power supply
- ◆ LED Power



Absolute Maximum Ratings $T_c = 25^\circ \text{C}$ unless otherwise noted

Symbol	Parameter	Limit	Unit
		TO-220F	
V_{DS}	Drain-Source Voltage ^a	500	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-Continuous, $T_c = 25^\circ \text{C}$	5	A
	Drain Current-Continuous, $T_c = 100^\circ \text{C}$	3	A
I_{DM}	Drain Current-Pulsed ^b	20	A
P_D	Maximum Power Dissipation @ $T_J = 25^\circ \text{C}$	30	W
EAS	Single Pulsed Avalanche Energy ^d	125	mJ
T_J, T_{STG}	Operating and Store Temperature Range	-55 to 150	$^\circ \text{C}$

Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-Case Max.	4.17	$^\circ \text{C/W}$

Electrical Characteristics $T_J = 25^\circ \text{C}$ unless otherwise noted

Off Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	500	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 500V, V_{GS} = 0V$	-	-	1	μA
I_{GSS}	Forward Gate Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 30V$	-	-	± 100	nA



MPF05N50

N-Channel Power MOSFET

■ On Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2	-	4	V
$R_{DS(on)}$	Static Drain-Source On-Resistance ^c	$V_{GS} = 10V, I_D = 2.5A$	-	1.35	1.55	Ω

■ Dynamic Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
C_{iss}	Input Capacitance	$V_{DS} = 25V,$ $V_{GS} = 0V,$ $f = 1.0MHz$	-	545	-	pF
C_{oss}	Output Capacitance		-	63	-	pF
C_{rss}	Reverse Transfer Capacitance		-	5.5	-	pF

■ On Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 250V, I_D = 5A,$ $V_{GS} = 10V$	-	9	-	ns
t_r	Turn-On Rise Time		-	11	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	29	-	ns
t_f	Turn-Off Fall Time		-	16	-	ns
Q_g	Total Gate Charge	$V_{DS} = 400V, I_D = 5A,$ $V_{GS} = 10V$	-	13	-	nC
Q_{gs}	Gate-Source Charge		-	3.3	-	nC
Q_{gd}	Gate-Drain Charge		-	5	-	nC

■ Drain-Source Diode Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
I_S	Drain-Source Diode Forward Continuous Current	$V_{GS} = 0V$	-	-	5	A
I_{SM}	Maximum Pulsed Current	$V_{GS} = 0V$	-	-	20	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0V, I_S = 10A$	-	-	1.4	V

Notes:

- $T_J = +25^\circ C$ to $+150^\circ C$
- Repetitive rating; pulse width limited by maximum junction temperature.
- Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$
- $L = 10mH, I_{AS} = 5A$

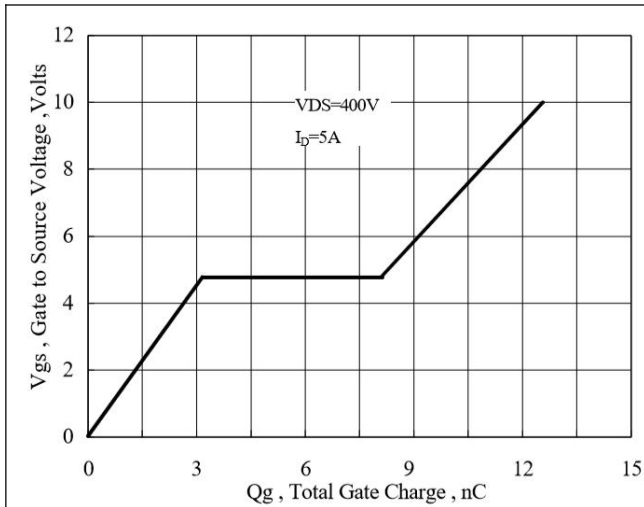


Figure 1. Gate Charge Characteristics

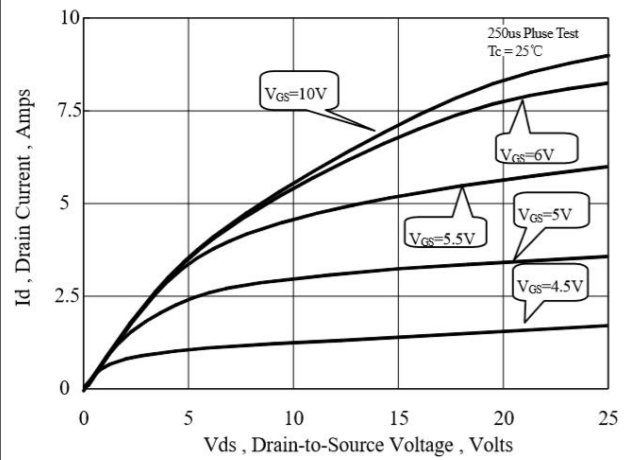


Figure 2. On-State Characteristics

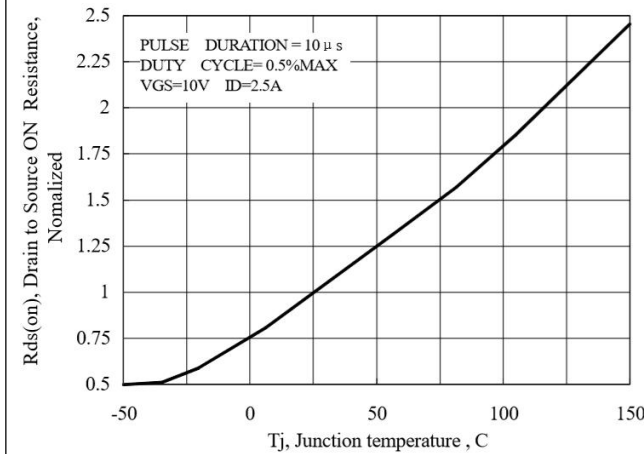


Figure 3. Normalized On-Resistance Variation with Temperature

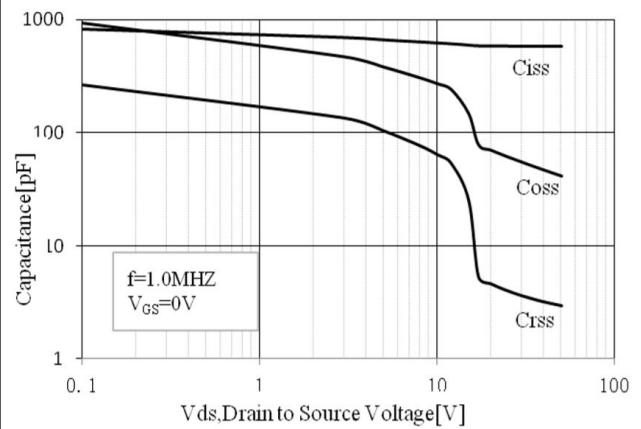


Figure 4. Typical Capacitance vs Drain to Source Voltage

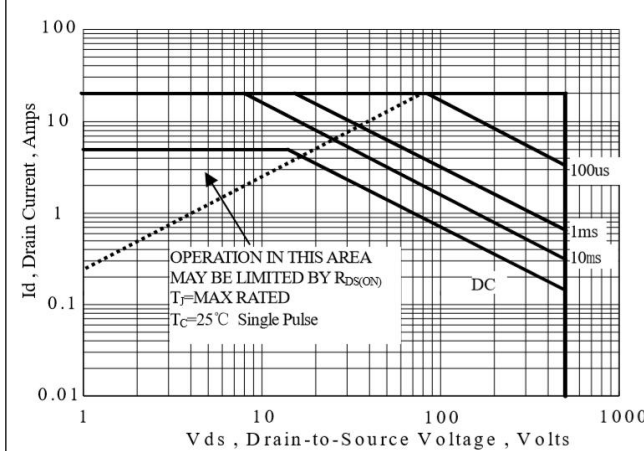


Figure 5 Maximum Forward Bias Safe Operating Area
TO-220F

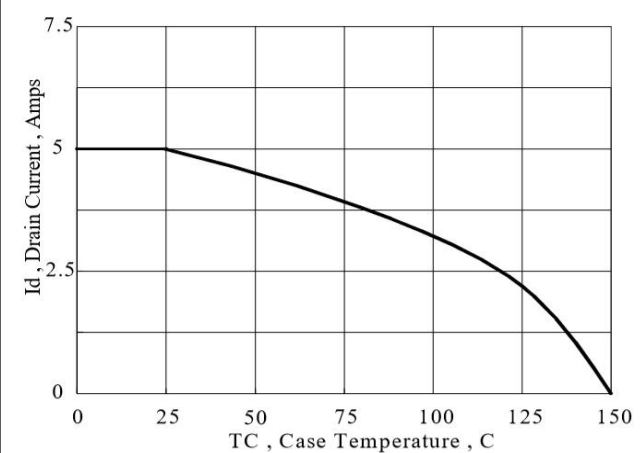
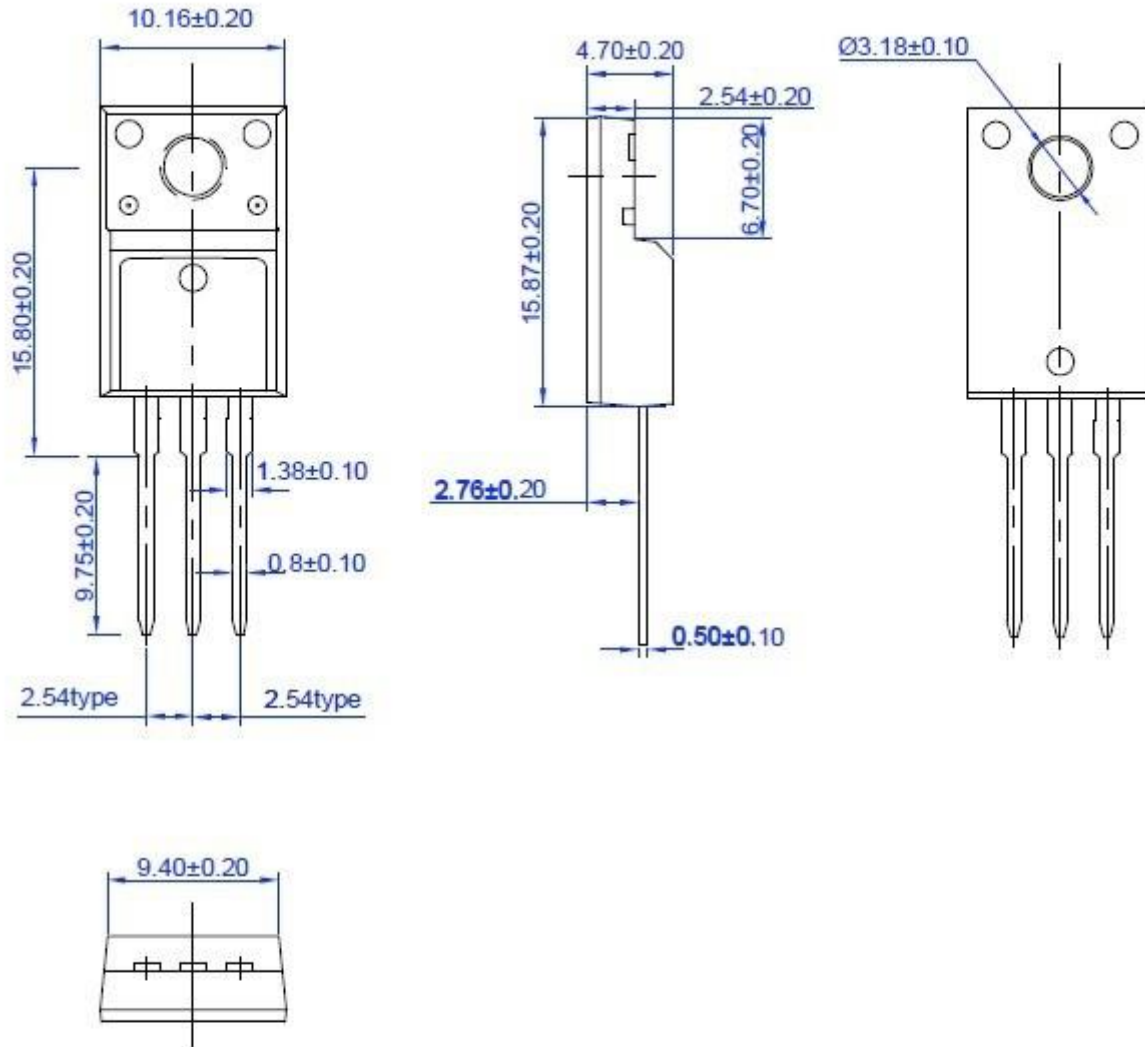


Figure 6. Maximum Continuous Drain Current vs Case Temperature

■ Package Information



技术要求:

1. 图中所指亚光面对应表面粗糙度 $Ra0.8$, 光面对应表面粗糙度为 $Ra0.2$
2. 上、下塑封体错位 ≤ 0.1 ; 塑封体中心与引线框架中心错位 ≤ 0.1
3. 塑封体外形未注棱边 $R0.2$
4. 未标注公差 ± 0.15